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Kind regards,

Team Nexperia

74ALVCH16952

16-bit registered transceiver; 3-state

Rev. 02 — 27 April 2006

Product data sheet

1. General description

The 74ALVCH16952 consists of two sections, each containing a dual octal non-inverting registered transceiver. Two 8-bit back to back registers store data flowing in both directions between two bidirectional buses. Data applied to the inputs is entered and stored on the rising edge of the clock ($nCPAB$ and $nCPBA$) provided that the clock enable ($nCEAB$ and $nCEBA$) is LOW. The data is then present at the output buffers, but is only accessible when the output enable input ($nOEAB$ and $nOEBA$) is LOW. Data flow from A inputs to B outputs is the same as for B inputs to A outputs.

2. Features

- CMOS low-power consumption
- Multibyte flow-through pinout architecture
- Low inductance, multiple center power and ground pins for minimum noise and ground bounce
- Direct interface with TTL levels
- Output drive capability 50 Ω transmission lines at 85 °C
- Complies with JEDEC standard JESD8-B

3. Quick reference data

Table 1. Quick reference data

$GND = 0 V$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; $t_r = t_f = 2.5\text{ ns}$.

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-----------|-------------------------------------|--|-----|-----|-----|------|
| t_{PHL} | propagation delay | | | | | |
| t_{PLH} | $nCPBA$ to nAn ; $nCPAB$ to nBn | $V_{CC} = 3.3\text{ V}$; $C_L = 50\text{ pF}$ | - | 3.2 | - | ns |
| | | $V_{CC} = 2.5\text{ V}$; $C_L = 30\text{ pF}$ | - | 3.2 | - | ns |
| f_{max} | maximum input clock frequency | $V_{CC} = 3.3\text{ V}$ | - | 350 | - | MHz |
| C_i | input capacitance | | - | 3.0 | - | pF |
| C_{PD} | power dissipation capacitance | per buffer; $V_i = GND$ to V_{CC} | [1] | 30 | - | pF |

[1] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in Volts;

N = number of inputs switching;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

PHILIPS

4. Ordering information

Table 2. Ordering information

| Type number | Package | | | Version |
|-------------|-------------------|---------|--|----------|
| | Temperature range | Name | Description | |
| DGG | -40 °C to +85 °C | TSSOP56 | plastic thin shrink small outline package; 56 leads; body width 6.1 mm | SOT364-1 |

5. Functional diagram

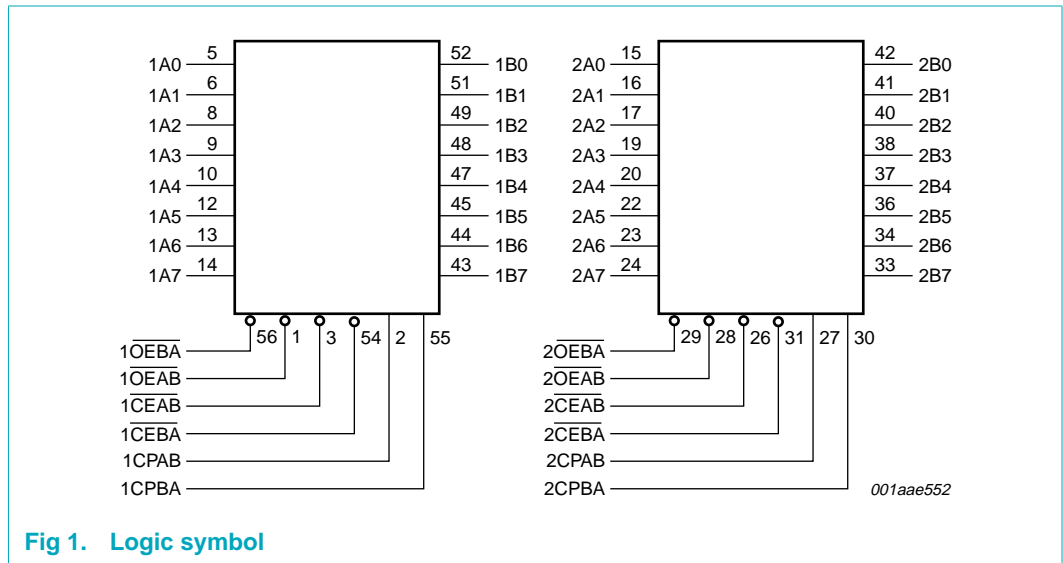


Fig 1. Logic symbol

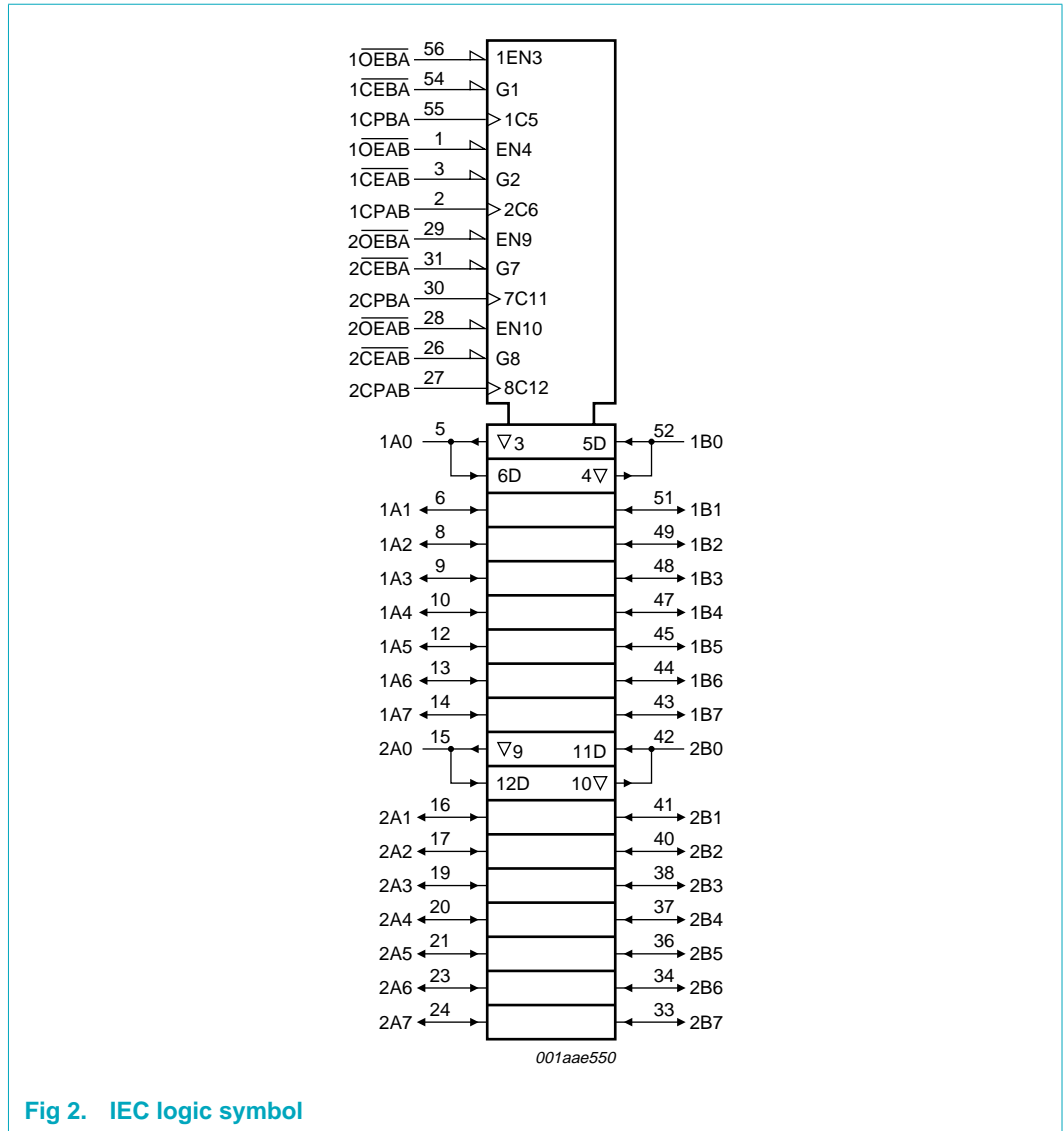


Fig 2. IEC logic symbol

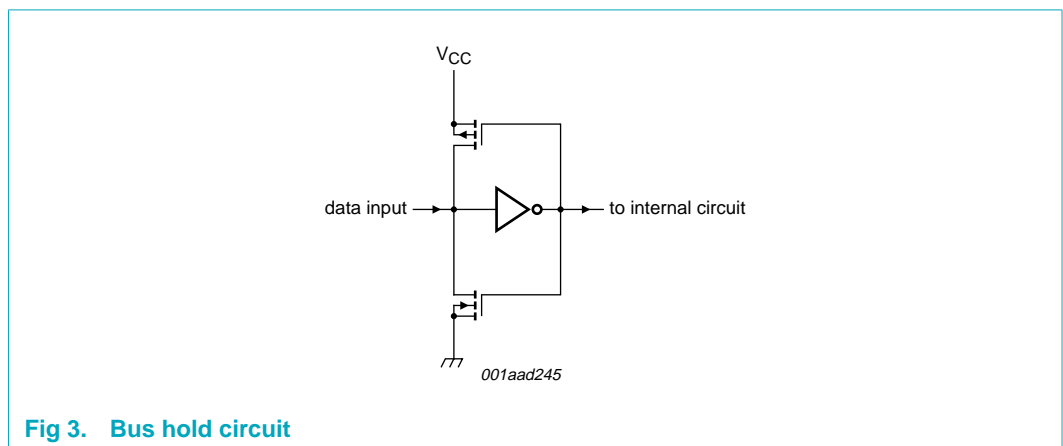


Fig 3. Bus hold circuit

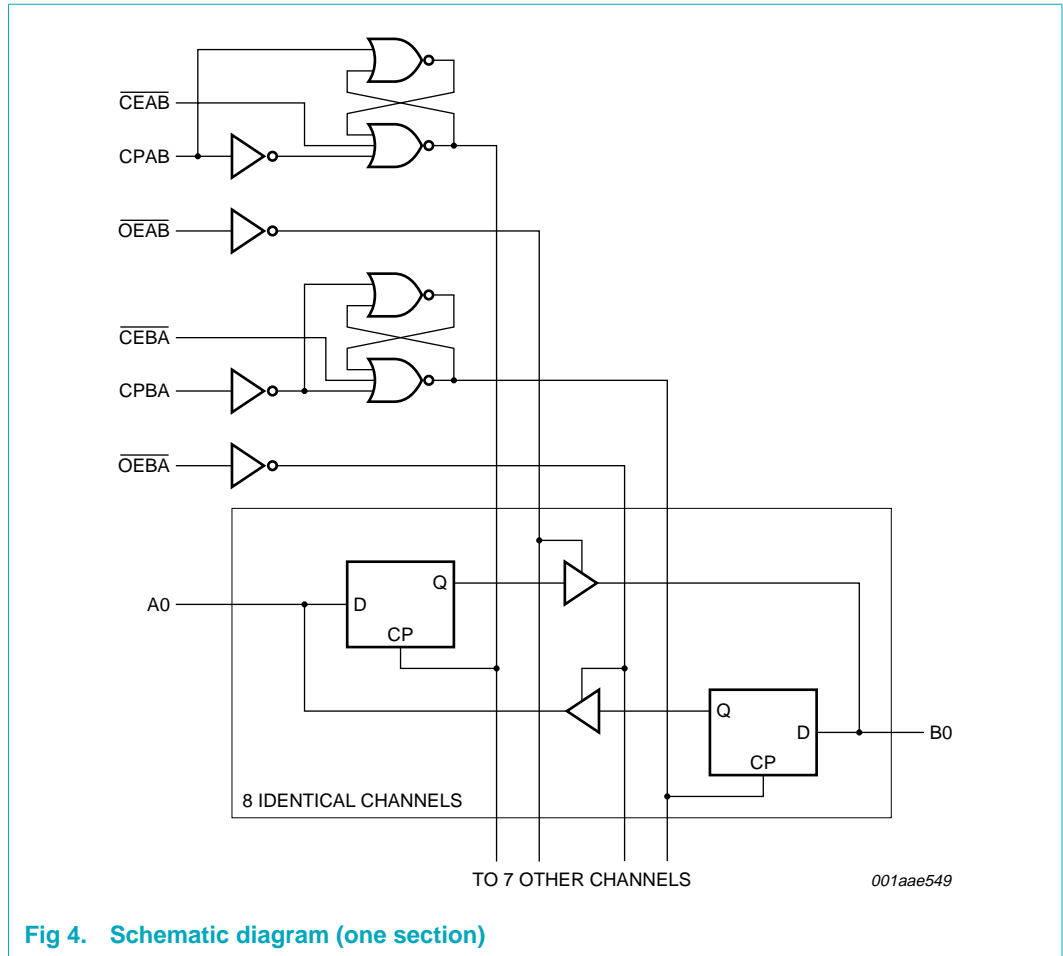
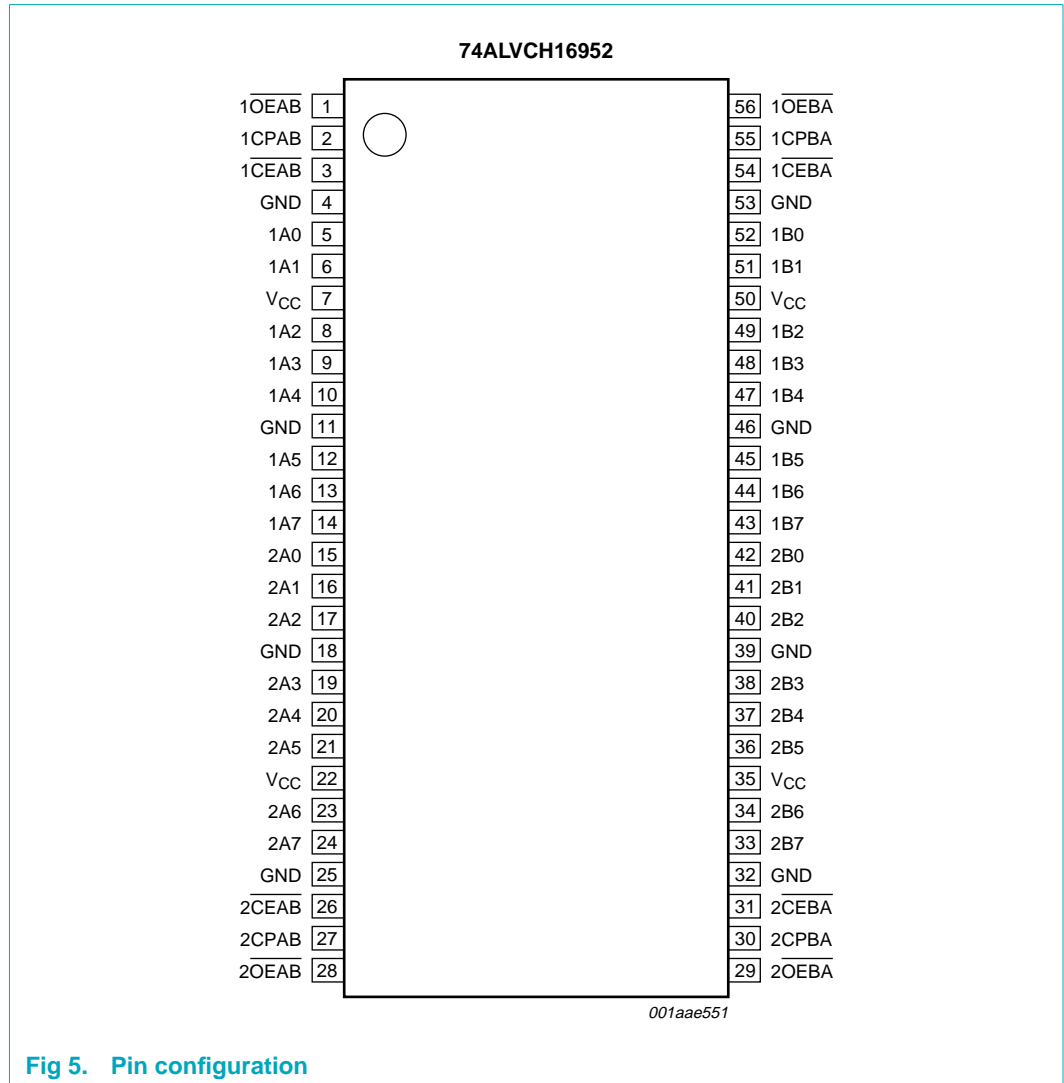


Fig 4. Schematic diagram (one section)

6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

| Symbol | Pin | Description |
|-----------------|-----|--|
| 1OEAB | 1 | output enable input (active LOW) |
| 1CPAB | 2 | clock pulse input (active rising edge) |
| 1CEAB | 3 | clock enable input (active LOW) |
| GND | 4 | ground (0 V) |
| 1A0 | 5 | data input or output 1A0 |
| 1A1 | 6 | data input or output 1A1 |
| V _{CC} | 7 | supply voltage |

Table 3. Pin description ...continued

| Symbol | Pin | Description |
|--------------------|-----|--|
| 1A2 | 8 | data input or output 1A2 |
| 1A3 | 9 | data input or output 1A3 |
| 1A4 | 10 | data input or output 1A4 |
| GND | 11 | ground (0 V) |
| 1A5 | 12 | data input or output 1A5 |
| 1A6 | 13 | data input or output 1A6 |
| 1A7 | 14 | data input or output 1A7 |
| 2A0 | 15 | data input or output 2A0 |
| 2A1 | 16 | data input or output 2A1 |
| 2A2 | 17 | data input or output 2A2 |
| GND | 18 | ground (0 V) |
| 2A3 | 19 | data input or output 2A3 |
| 2A4 | 20 | data input or output 2A4 |
| 2A5 | 21 | data input or output 2A5 |
| V _{CC} | 22 | supply voltage |
| 2A6 | 23 | data input or output 2A6 |
| 2A7 | 24 | data input or output 2A7 |
| GND | 25 | ground (0 V) |
| $\overline{2CEAB}$ | 26 | clock enable input (active LOW) |
| 2CPAB | 27 | clock pulse input (active rising edge) |
| $\overline{2OEAB}$ | 28 | output enable input (active LOW) |
| $\overline{2OEBA}$ | 29 | output enable input (active LOW) |
| 2CPBA | 30 | clock pulse input (active rising edge) |
| $\overline{2CEBA}$ | 31 | clock enable input (active LOW) |
| GND | 32 | ground (0 V) |
| 2B7 | 33 | data input or output 2B7 |
| 2B6 | 34 | data input or output 2B6 |
| V _{CC} | 35 | supply voltage |
| 2B5 | 36 | data input or output 2B5 |
| 2B4 | 37 | data input or output 2B4 |
| 2B3 | 38 | data input or output 2B3 |
| GND | 39 | ground (0 V) |
| 2B2 | 40 | data input or output 2B2 |
| 2B1 | 41 | data input or output 2B1 |
| 2B0 | 42 | data input/output 2B0 |
| 1B7 | 43 | data input or output 1B7 |
| 1B6 | 44 | data input or output 1B6 |
| 1B5 | 45 | data input or output 1B5 |
| GND | 46 | ground (0 V) |
| 1B4 | 47 | data input or output 1B4 |
| 1B3 | 48 | data input or output 1B3 |

Table 3. Pin description ...continued

| Symbol | Pin | Description |
|----------------------------|-----|--|
| 1B2 | 49 | data input or output 1B2 |
| V _{CC} | 50 | supply voltage |
| 1B1 | 51 | data input or output 1B1 |
| 1B0 | 52 | data input or output 1B0 |
| GND | 53 | ground (0 V) |
| 1 $\overline{\text{CEBA}}$ | 54 | clock enable input (active LOW) |
| 1CPBA | 55 | clock pulse input (active rising edge) |
| 1 $\overline{\text{OEBA}}$ | 56 | output enable input (active LOW) |

7. Functional description

7.1 Function table

Table 4. Function table^{[1][2]}

| Operating mode | Control | | | Input | Internal | Output |
|-------------------------|----------------------------|----------------------------|-------|-------|----------|--------|
| | n $\overline{\text{OEAB}}$ | n $\overline{\text{CEAB}}$ | nCPAB | nAn | nQn | nBn |
| Hold | L | H | X | X | NC | NC |
| Load and output enable | L | L | ↑ | L | L | L |
| | | | | H | H | H |
| Load and output disable | H | L | ↑ | L | L | Z |
| | | | | H | H | Z |

[1] A-to-B data flow is shown; B-to-A data flow is similar, but uses signals n $\overline{\text{OEBA}}$, n $\overline{\text{CEBA}}$ and nCPBA

[2] H = HIGH voltage level;
 L = LOW voltage level;
 ↑ = LOW-to-HIGH transition;
 X = don't care;
 Z = high impedance OFF-state;
 NC = no change.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|-----------|--------------------------|-----------------------------------|----------|----------------|------|
| V_{CC} | supply voltage | | -0.5 | +4.6 | V |
| V_I | input voltage | control pins | [1] -0.5 | +4.6 | V |
| | | data inputs | [1] -0.5 | $V_{CC} + 0.5$ | V |
| V_O | output voltage | | [1] -0.5 | $V_{CC} + 0.5$ | V |
| I_{IK} | input clamping current | $V_I < 0$ V | - | -50 | mA |
| I_{OK} | output clamping current | $V_O > V_{CC}$ or $V_O < 0$ V | - | ± 50 | mA |
| I_O | output current | $V_O = 0$ V to V_{CC} | - | ± 50 | mA |
| I_{CC} | quiescent supply current | | - | 100 | mA |
| I_{GND} | ground current | | - | -100 | mA |
| T_{stg} | storage temperature | | -65 | +150 | °C |
| P_{tot} | total power dissipation | $T_{amb} = -40$ °C to +125 °C [2] | - | 600 | mW |

[1] The input and output negative voltage ratings may be exceeded if the input and output current ratings are observed.

[2] P_{tot} derates linearly with 8 mW/K above 55 °C.

9. Recommended operating conditions

Table 6. Recommended operating conditions

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---------------------|-------------------------------------|---------------------------|---------|-----|----------|------|
| V_{CC} | supply voltage | $C_L = 30$ pF | [1] 2.3 | - | 2.7 | V |
| | | $C_L = 50$ pF | [1] 3.0 | - | 3.6 | V |
| V_I | input voltage | | 0 | - | V_{CC} | V |
| V_O | output voltage | | 0 | - | V_{CC} | V |
| T_{amb} | ambient temperature | in free-air | -40 | - | +85 | °C |
| $\Delta t/\Delta V$ | input transition rise and fall rate | $V_{CC} = 2.3$ V to 3.0 V | 0 | - | 20 | ns/V |
| | | $V_{CC} = 3.0$ V to 3.6 V | 0 | - | 10 | ns/V |

[1] Maximum speed performance.

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|-------------------------------------|---|-----------------------|------------------------|------|------|
| T_{amb} = -40 °C to +85 °C^[1] | | | | | | |
| V _{IH} | HIGH-state input voltage | V _{CC} = 2.3 V to 2.7 V | 1.7 | 1.2 | - | V |
| | | V _{CC} = 2.7 V to 3.6 V | 2.0 | 1.5 | - | V |
| V _{IL} | LOW-state input voltage | V _{CC} = 2.3 V to 2.7 V | - | 1.2 | 0.7 | V |
| | | V _{CC} = 2.7 V to 3.6 V | - | 1.5 | 0.8 | V |
| V _{OH} | HIGH-state output voltage | V _I = V _{IH} or V _{IL} | | | | |
| | | I _{OH} = -100 µA; V _{CC} = 2.3 V to 3.6 V | V _{CC} - 0.2 | V _{CC} | - | V |
| | | I _{OH} = -6 mA; V _{CC} = 2.3 V | V _{CC} - 0.3 | V _{CC} - 0.08 | - | V |
| | | I _{OH} = -12 mA; V _{CC} = 2.3 V | V _{CC} - 0.6 | V _{CC} - 0.26 | - | V |
| | | I _{OH} = -12 mA; V _{CC} = 2.7 V | V _{CC} - 0.5 | V _{CC} - 0.14 | - | V |
| | | I _{OH} = -12 mA; V _{CC} = 3.0 V | V _{CC} - 0.6 | V _{CC} - 0.09 | - | V |
| | | I _{OH} = -24 mA; V _{CC} = 3.0 V | V _{CC} - 1.0 | V _{CC} - 0.28 | - | V |
| V _{OL} | LOW-state output voltage | V _I = V _{IH} or V _{IL} | | | | |
| | | I _{OL} = 100 µA; V _{CC} = 2.3 V to 3.6 V | - | GND | 0.20 | V |
| | | I _{OL} = 6 mA; V _{CC} = 2.3 V | - | 0.07 | 0.40 | V |
| | | I _{OL} = 12 mA; V _{CC} = 2.3 V | - | 0.15 | 0.70 | V |
| | | I _{OL} = 12 mA; V _{CC} = 2.7 V | - | 0.14 | 0.40 | V |
| | | I _{OL} = 24 mA; V _{CC} = 3.0 V | - | 0.27 | 0.55 | V |
| I _{LI} | input leakage current | V _{CC} = 2.3 V to 3.6 V; V _I = V _{CC} or GND | - | 0.1 | 5 | µA |
| I _{OZ} | off-state output current | V _{CC} = 2.7 V to 3.6 V; V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND | - | 0.1 | 10 | µA |
| I _{CC} | quiescent supply current | V _{CC} = 2.3 V to 3.6 V; V _I = V _{CC} or GND; I _O = 0 A | - | 0.2 | 40 | µA |
| ΔI _{CC} | additional quiescent supply current | V _{CC} = 2.3 V to 3.6 V; V _I = V _{CC} - 0.6 V; I _O = 0 A | - | 150 | 750 | µA |
| I _{BHL} | bus hold LOW sustaining current | V _{CC} = 2.3 V; V _I = 0.7 V | [2] 45 | - | - | µA |
| | | V _{CC} = 3.0 V; V _I = 0.8 V | [2] 75 | 150 | - | µA |
| I _{BHH} | bus hold HIGH sustaining current | V _{CC} = 2.3 V; V _I = 1.7 V | [2] -45 | - | - | µA |
| | | V _{CC} = 3.0 V; V _I = 2.0 V | [2] -75 | -175 | - | µA |
| I _{BHLO} | bus hold LOW overdrive current | V _{CC} = 3.6 V | [2] 500 | - | - | µA |
| I _{BHHO} | bus hold HIGH overdrive current | V _{CC} = 3.6 V | [2] -500 | - | - | µA |
| C _i | input capacitance | | - | 3.0 | - | pF |

[1] Typical values are measured at T_{amb} = 25 °C.

[2] Valid for data inputs of bus hold parts.

11. Dynamic characteristics

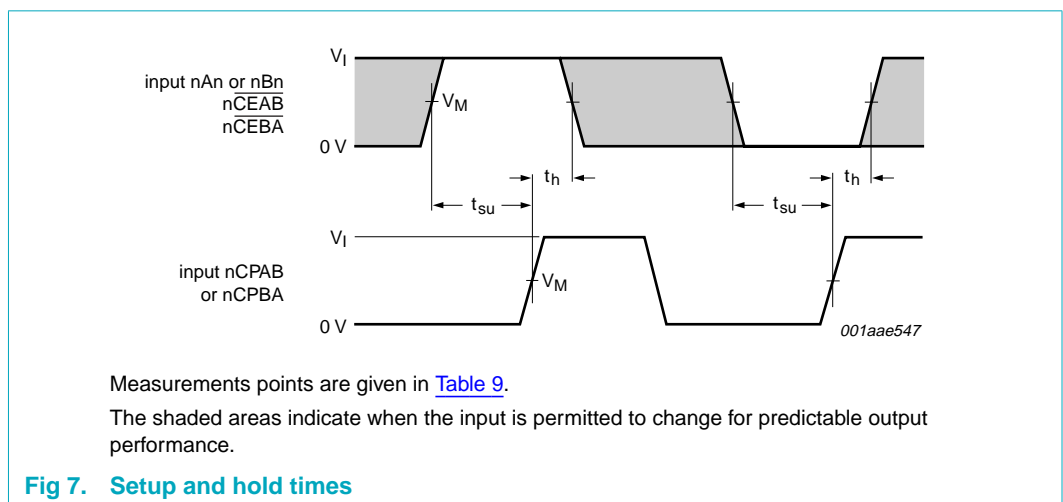
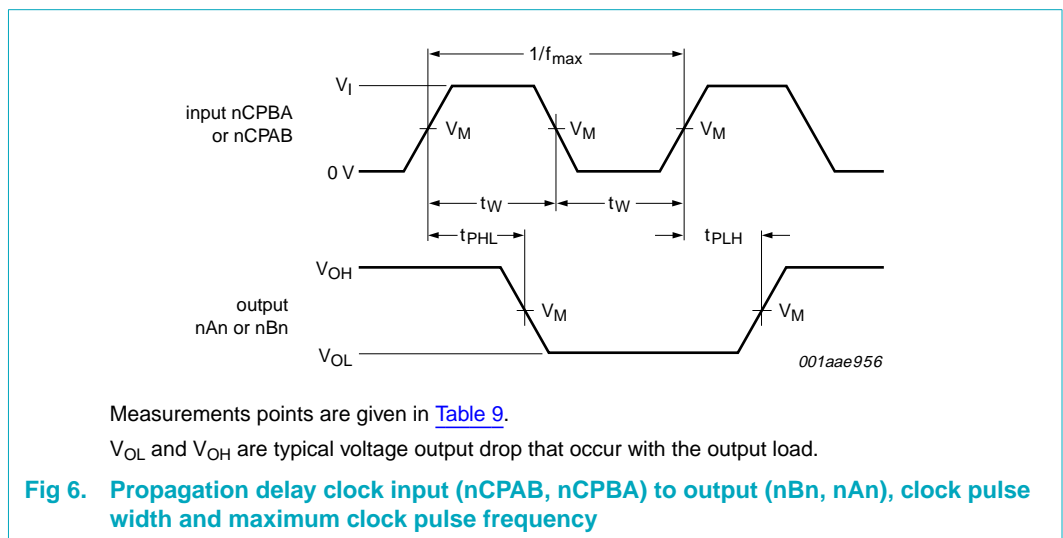
Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 9](#).

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit | |
|--|---|---|--|-----|-----|------|----|
| $T_{amb} = -40\text{ }^{\circ}\text{C to } +85\text{ }^{\circ}\text{C}$[1] | | | | | | | |
| t_{PHL} , t_{PLH} | propagation delay nCPBA to nAn; nCPAB to nBn | see Figure 6 | | | | | |
| | | $V_{CC} = 2.3\text{ V to } 2.7\text{ V}$ | 1.0 | 3.2 | 4.1 | ns | |
| | | $V_{CC} = 2.7\text{ V}$ | 1.0 | - | 4.6 | ns | |
| | | $V_{CC} = 3.0\text{ V to } 3.6\text{ V}$ | 1.0 | 3.2 | 3.9 | ns | |
| t_{PZH} , t_{PZL} | 3-state output enable time $\overline{\text{nOEBA}}$ to nAn; nOEAB to nBn | see Figure 8 | | | | | |
| | | $V_{CC} = 2.3\text{ V to } 2.7\text{ V}$ | 1.0 | - | 5.4 | ns | |
| | | $V_{CC} = 2.7\text{ V}$ | 1.0 | - | 5.3 | ns | |
| | | $V_{CC} = 3.0\text{ V to } 3.6\text{ V}$ | 1.0 | - | 4.4 | ns | |
| t_{PHZ} , t_{PLZ} | 3-state output disable time $\overline{\text{nOEBA}}$ to nAn; nOEAB to nBn | see Figure 8 | | | | | |
| | | $V_{CC} = 2.3\text{ V to } 2.7\text{ V}$ | 1.0 | - | 5.3 | ns | |
| | | $V_{CC} = 2.7\text{ V}$ | 1.4 | - | 4.4 | ns | |
| | | $V_{CC} = 3.0\text{ V to } 3.6\text{ V}$ | 1.1 | - | 4.0 | ns | |
| t_W | pulse width HIGH or LOW nCPAB; nCPBA | see Figure 6 | | | | | |
| | | $V_{CC} = 2.3\text{ V to } 2.7\text{ V}$ | 3.3 | - | - | ns | |
| | | $V_{CC} = 2.7\text{ V}$ | 3.3 | - | - | ns | |
| | | $V_{CC} = 3.0\text{ V to } 3.6\text{ V}$ | 3.3 | - | - | ns | |
| t_{su} | setup time nAn to nCPAB or nBn to nCPBA | see Figure 7 | | | | | |
| | | $V_{CC} = 2.3\text{ V to } 2.7\text{ V}$ | 1.7 | - | - | ns | |
| | | $V_{CC} = 2.7\text{ V}$ | 1.9 | - | - | ns | |
| | | | $V_{CC} = 3.0\text{ V to } 3.6\text{ V}$ | 1.5 | - | - | ns |
| | nCEAB to nCPAB or nCEBA to nCPBA | $V_{CC} = 2.3\text{ V to } 2.7\text{ V}$ | 1.2 | - | - | ns | |
| | | $V_{CC} = 2.7\text{ V}$ | 1.0 | - | - | ns | |
| $V_{CC} = 3.0\text{ V to } 3.6\text{ V}$ | | 1.0 | - | - | ns | | |
| t_h | hold time nAn to nCPAB or nBn to nCPBA | see Figure 7 | | | | | |
| | | $V_{CC} = 2.3\text{ V to } 2.7\text{ V}$ | 0.6 | - | - | ns | |
| | | $V_{CC} = 2.7\text{ V}$ | 0.6 | - | - | ns | |
| | | | $V_{CC} = 3.0\text{ V to } 3.6\text{ V}$ | 0.8 | - | - | ns |
| | nCEAB to nCPAB or nCEBA to nCPBA | $V_{CC} = 2.3\text{ V to } 2.7\text{ V}$ | 1.1 | - | - | ns | |
| | | $V_{CC} = 2.7\text{ V}$ | 0.9 | - | - | ns | |
| $V_{CC} = 3.0\text{ V to } 3.6\text{ V}$ | | 1.1 | - | - | ns | | |
| f_{max} | maximum clock pulse frequency | see Figure 6 | | | | | |
| | | $V_{CC} = 2.3\text{ V to } 2.7\text{ V}$ | 150 | 350 | - | MHz | |
| | | $V_{CC} = 2.7\text{ V}$ | 150 | 350 | - | MHz | |
| | | $V_{CC} = 3.0\text{ V to } 3.6\text{ V}$ | 150 | 350 | - | MHz | |
| C_{PD} | power dissipation capacitance | per buffer; $V_1 = \text{GND to } V_{CC}$ | [2] | - | 30 | pF | |

- [1] Typical values are measured at nominal supply voltage and at $T_{amb} = 25\text{ }^{\circ}\text{C}$.
- [2] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz;
 f_o = output frequency in MHz;
 C_L = output load capacitance in pF;
 V_{CC} = supply voltage in Volts;
 N = number of inputs switching;
 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

12. Waveforms



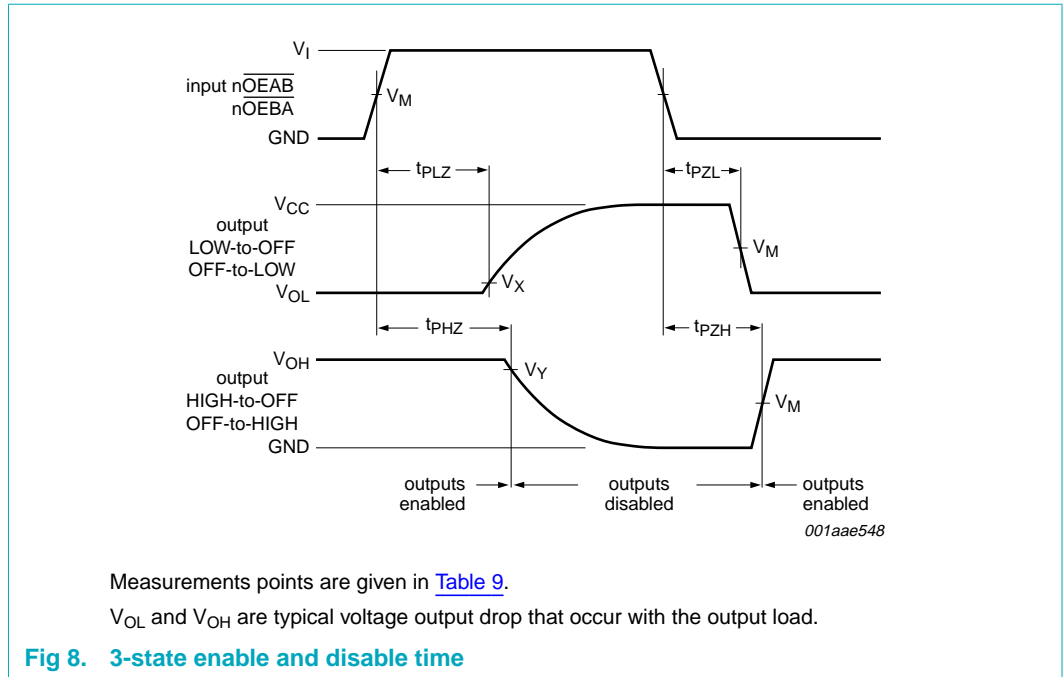


Table 9. Measurement points

| Supply voltage | Input | | Output | | |
|----------------|----------|-------|--------|-------------------|-------------------|
| V_{CC} | V_I | V_M | V_M | V_X | V_Y |
| 2.3 V to 2.7 V | V_{CC} | 0.5 V | 0.5 V | $V_{OL} + 0.15 V$ | $V_{OH} - 0.15 V$ |
| 2.7 V | 2.7 V | 1.5 V | 1.5 V | $V_{OL} + 0.3 V$ | $V_{OH} - 0.3 V$ |
| 3.0 V to 3.6 V | 2.7 V | 1.5 V | 1.5 V | $V_{OL} + 0.3 V$ | $V_{OH} - 0.3 V$ |

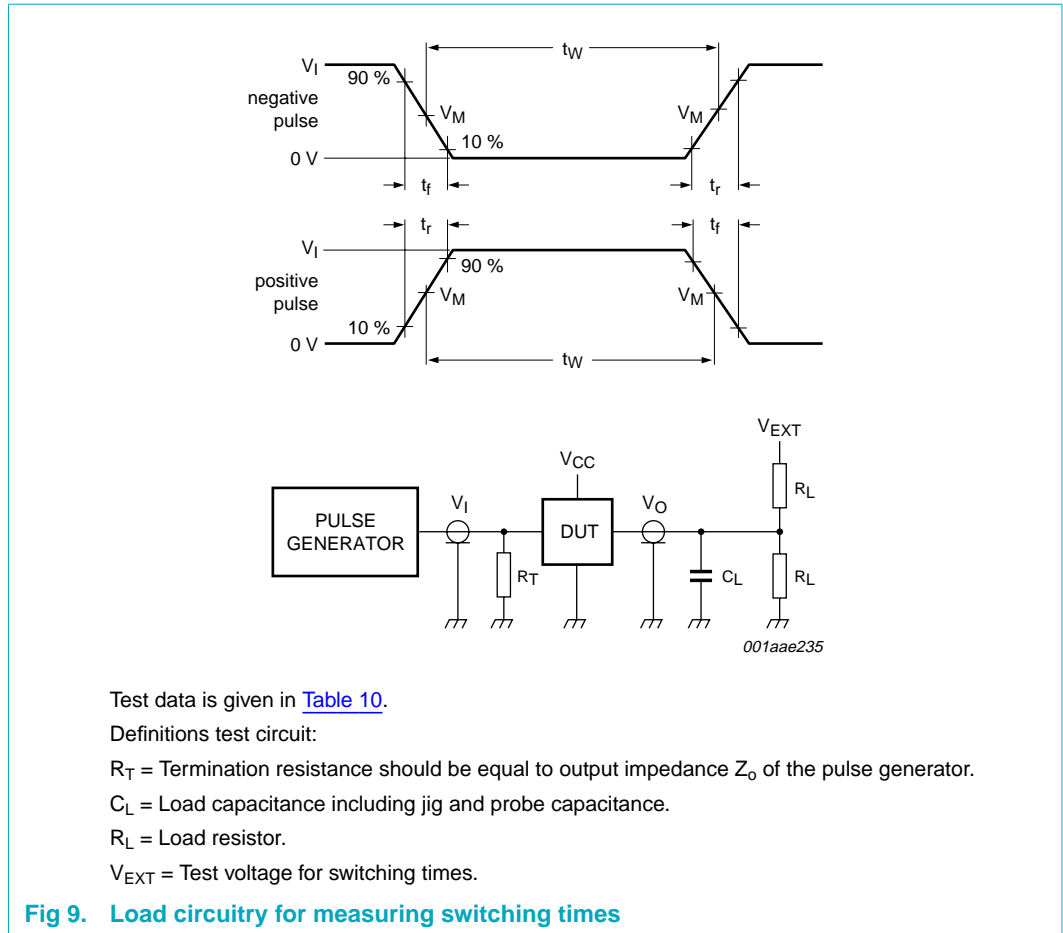


Table 10. Test data

| Supply voltage | Input | | Load | | V_{EXT} | | |
|----------------|----------|---------------|-------|--------------|--------------------|--------------------|--------------------|
| | V_I | t_r, t_f | C_L | R_L | t_{PLH}, t_{PHL} | t_{PLZ}, t_{PZL} | t_{PHZ}, t_{PZH} |
| 2.3 V to 2.7 V | V_{CC} | ≤ 2.0 ns | 30 pF | 500 Ω | open | $2 \times V_{CC}$ | GND |
| 2.7 V | 2.7 V | 2.5 ns | 50 pF | 500 Ω | open | $2 \times V_{CC}$ | GND |
| 3.0 V to 3.6 V | 2.7 V | 2.5 ns | 50 pF | 500 Ω | open | $2 \times V_{CC}$ | GND |

13. Package outline

TSSOP56: plastic thin shrink small outline package; 56 leads; body width 6.1 mm

SOT364-1

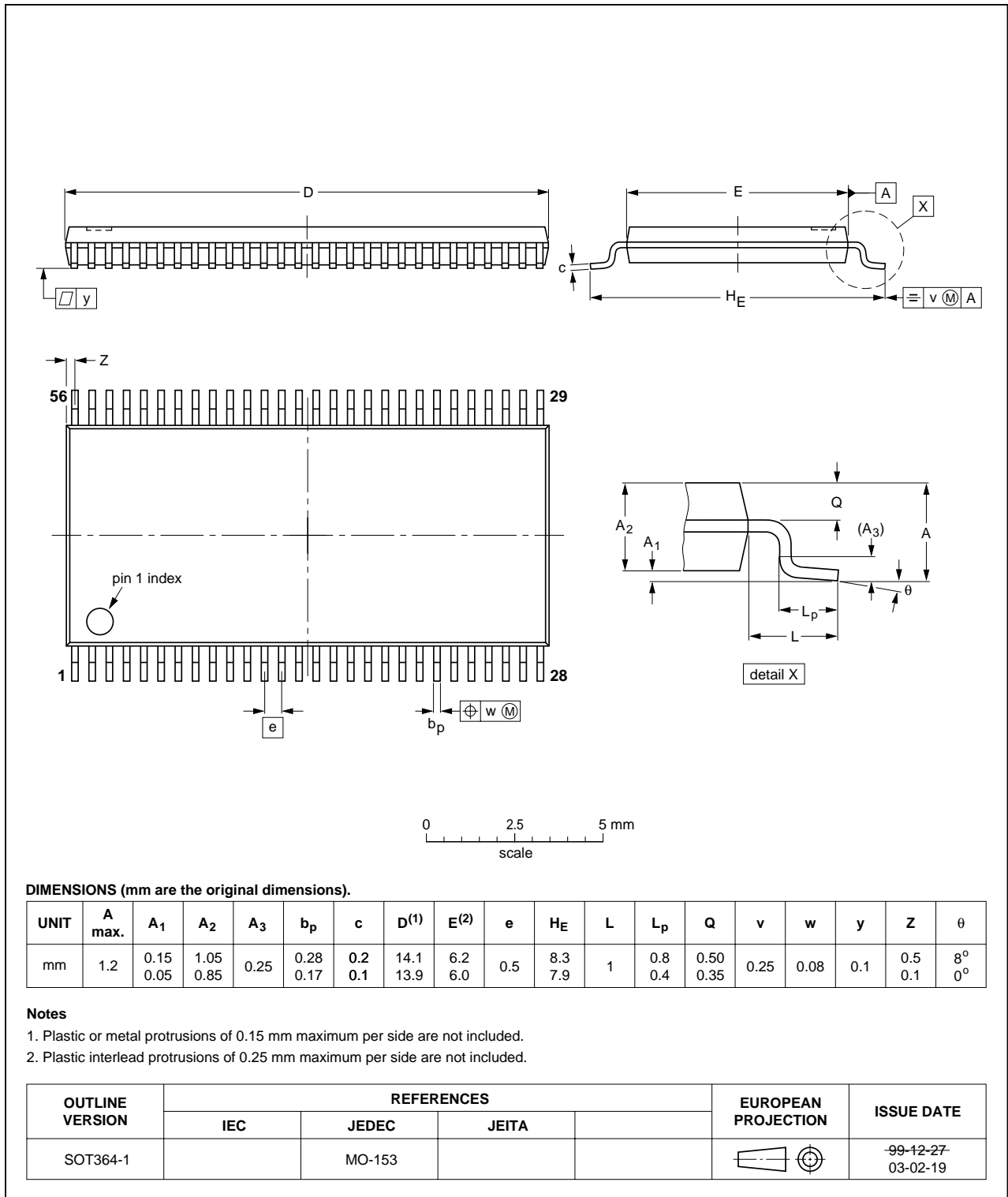


Fig 10. Package outline SOT364-1 (TSSOP56)

14. Abbreviations

Table 11. Abbreviations

| Acronym | Description |
|---------|---|
| CMOS | Complementary Metal Oxide Semiconductor |
| DUT | Device Under Test |
| TTL | Transistor-Transistor Logic |

15. Revision history

Table 12. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|------------------------------------|--------------|---|---------------|----------------|
| 74ALVCH16952_2 | 20060427 | Product data sheet | - | 74ALVCH16952_1 |
| Modifications: | | <ul style="list-style-type: none">The format of this data sheet has been redesigned to comply with the new presentation and information standard of Philips SemiconductorsThe symbol of pin numbers 15, 16, 17, 19, 20, 21, 23 and 24 is rectified | | |
| 74ALVCH16952_1 (9397 750 04563) | 19980901 | Preliminary specification | - | - |

16. Legal information

16.1 Data sheet status

| Document status ^{[1][2]} | Product status ^[3] | Definition |
|-----------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.semiconductors.philips.com>.

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